NTMFS4C35N

MOSFET – Power, Single, N-Channel, SO-8 FL
30 V, 80 A

Features
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Applications
- CPU Power Delivery
- DC−DC Converters

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	30	V
Gate−to−Source Voltage			V_{GS}	±20	V
Continuous Drain Current $R_{\theta JA}$ (Note 1)	Steady State	T_A = 25°C	I_D	22.5	A
		T_A = 80°C		16.8	
Power Dissipation $R_{\theta JA}$ (Note 1)		T_A = 25°C	P_D	2.59	W
Continuous Drain Current $R_{\theta JA} \le 10$ s (Note 1)		T_A = 25°C	I_D	36	A
		T_A = 80°C		27	
Power Dissipation $R_{\theta JA} \le 10$ s (Note 1)		T_A = 25°C	P_D	6.65	W
Continuous Drain Current $R_{\theta JA}$ (Note 2)		T_A = 25°C	I_D	12.4	A
		T_A = 80°C		9.3	
Power Dissipation $R_{\theta JA}$ (Note 2)		T_A = 25°C	P_D	0.78	W
Continuous Drain Current $R_{\theta JC}$ (Note 1)		T_C = 25°C	I_D	80	A
		T_C =80°C		60	
Power Dissipation $R_{\theta JC}$ (Note 1)		T_C = 25°C	P_D	33	W
Pulsed Drain Current	T_A = 25°C, t_p = 10 μs		I_{DM}	180	A
Current Limited by Package		T_A = 25°C	I_{Dmax}	80	A
Operating Junction and Storage Temperature			T_J, T_{STG}	−55 to +150	°C
Source Current (Body Diode)			I_S	30	A
Drain to Source dV/dt			dV/d_t	7.0	V/ns
Single Pulse Drain−to−Source Avalanche Energy (T_J = 25°C, V_{GS} = 10 V, I_L = 48 A_{pk}, L = 0.1 mH, R_{GS} = 25 Ω) (Note 3)			E_{AS}	115	mJ
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. Surface−mounted on FR4 board using 1 sq−in pad, 1 oz Cu.

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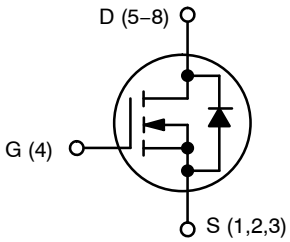
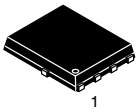
$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	I_D MAX
30 V	3.2 mΩ @ 10 V	80 A
	4.0 mΩ @ 4.5 V	

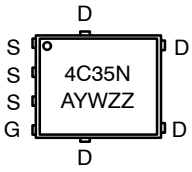


N−CHANNEL MOSFET



SO−8 FLAT LEAD CASE 488AA STYLE 1

MARKING DIAGRAM



A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceabililty

ORDERING INFORMATION

Device	Package	Shipping†
NTMFS4C35NT1G	SO−8 FL (Pb−Free)	1500 / Tape & Reel
NTMFS4C35NT3G	SO−8 FL (Pb−Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

2. Surface−mounted on FR4 board using the minimum recommended pad size.
3. This is the absolute maximum ratings. Parts are 100% tested at T_J = 25°C, V_{GS} = 10 V, I_L = 29 A, E_{AS} = 42 mJ.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction−to−Case (Drain)	$R_{\theta JC}$	3.8	°C/W
Junction−to−Ambient − Steady State (Note 4)	$R_{\theta JA}$	48.3	
Junction−to−Ambient − Steady State (Note 5)	$R_{\theta JA}$	159.3	
Junction−to−Ambient − (t ≤ 10 s) (Note 4)	$R_{\theta JA}$	18.8	

4. Surface−mounted on FR4 board using 1 sq−in pad, 1 oz Cu.
5. Surface−mounted on FR4 board using the minimum recommended pad size.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		30			V
Drain−to−Source Breakdown Voltage (transient)	$V_{(BR)DSSt}$	V_{GS} = 0 V, $I_{D(aval)}$ = 13.2 A, T_{case} = 25°C, $t_{transient}$ = 100 ns		34			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}$/T_J				12		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 24 V	T_J = 25°C			1.0	μA
			T_J = 125°C			10	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V				±100	nA
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 250 μA		1.3		2.2	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$				5.0		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 30 A		2.56	3.2	mΩ
		V_{GS} = 4.5 V	I_D = 30 A		3.4	4.0	
Forward Transconductance	g_{FS}	V_{DS} = 1.5 V, I_D = 15 A			50		S
Gate Resistance	R_G	T_A = 25°C			1.0		Ω
CHARGES AND CAPACITANCES							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1 MHz, V_{DS} = 15 V			2300		pF
Output Capacitance	C_{OSS}				1097		
Reverse Transfer Capacitance	C_{RSS}				46		
Capacitance Ratio	C_{RSS}/C_{ISS}	V_{GS} = 0 V, V_{DS} = 15 V, f = 1 MHz			0.02		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 4.5 V, V_{DS} = 15 V; I_D = 30 A			15		nC
Threshold Gate Charge	$Q_{G(TH)}$				3.3		
Gate−to−Source Charge	Q_{GS}				6.5		
Gate−to−Drain Charge	Q_{GD}				5.5		
Gate Plateau Voltage	V_{GP}				3.1		V
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 10 V, V_{DS} = 15 V; I_D = 30 A			32.5		nC
SWITCHING CHARACTERISTICS (Note 7)							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = 4.5 V, V_{DS} = 15 V, I_D = 15 A, R_G = 3.0 Ω			12.6		ns
Rise Time	t_r				33		
Turn−Off Delay Time	$t_{d(OFF)}$				21.4		
Fall Time	t_f				6.7		

6. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
7. Switching characteristics are independent of operating junction temperatures.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS (Note 7)							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = 10 V, V_{DS} = 15 V, I_D = 15 A, R_G = 3.0 Ω			8.7		ns
Rise Time	t_r				26		
Turn−Off Delay Time	$t_{d(OFF)}$				28		
Fall Time	t_f				4.4		
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 10 A	T_J = 25°C		0.8	1.1	V
			T_J = 125°C		0.62		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dI_S/dt = 100 A/μs, I_S = 30 A			41		ns
Charge Time	t_a				21		
Discharge Time	t_b				20		
Reverse Recovery Charge	Q_{RR}				30		nC

6. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
7. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

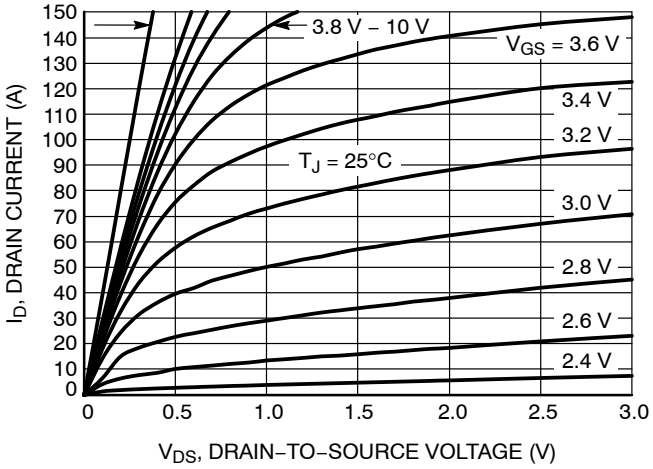


Figure 1. On−Region Characteristics

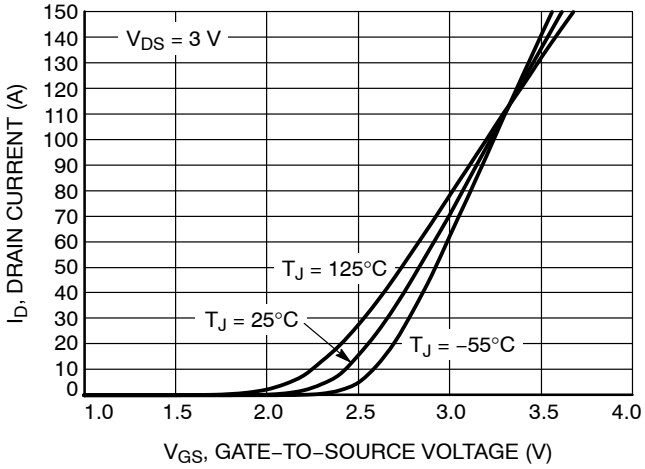


Figure 2. Transfer Characteristics

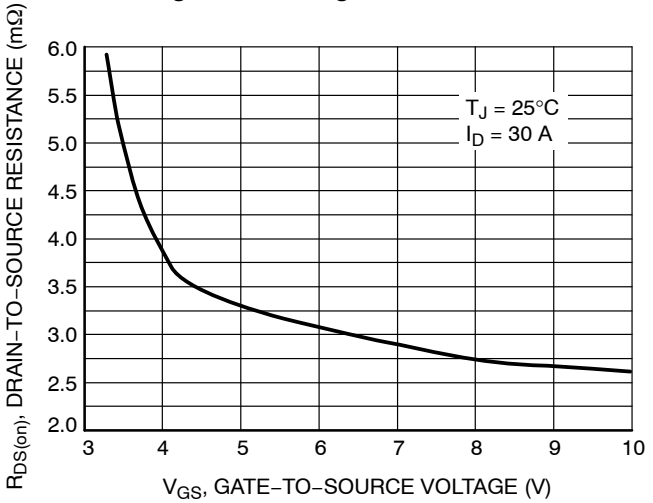


Figure 3. On−Resistance vs. V_{GS}

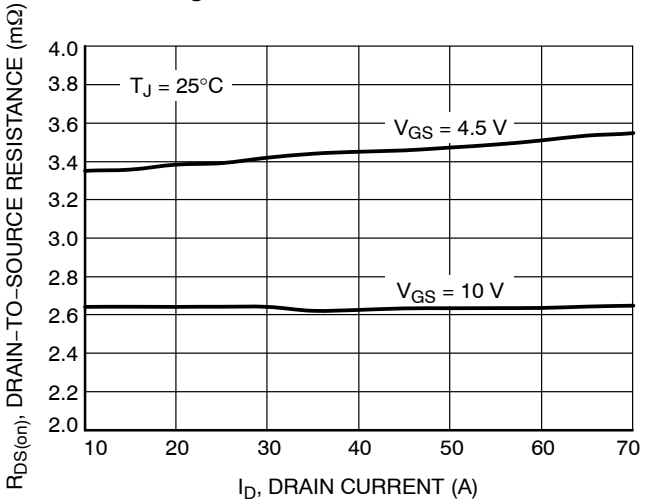


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

TYPICAL CHARACTERISTICS

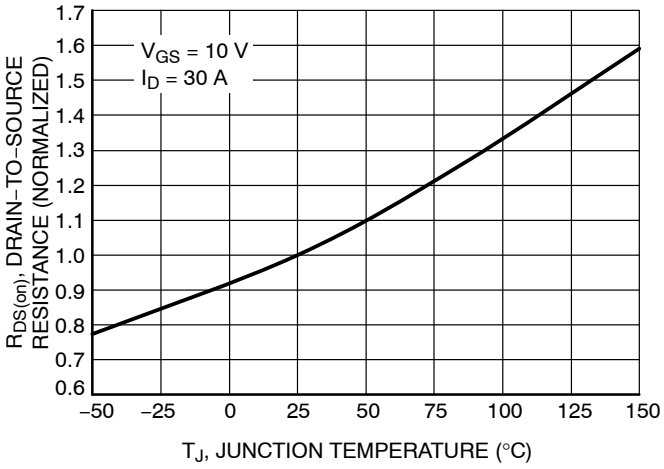


Figure 5. On−Resistance Variation with Temperature

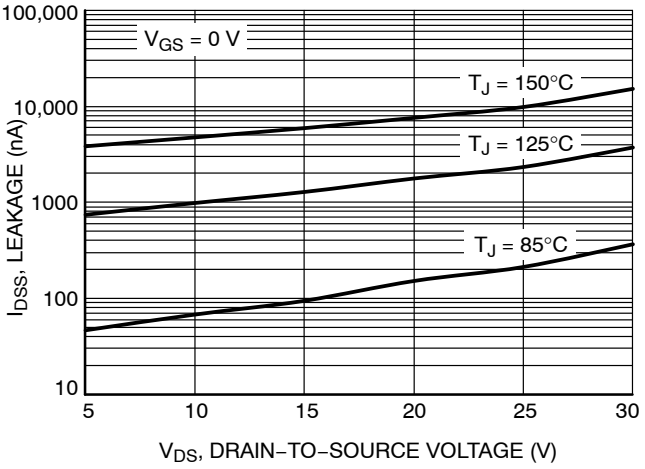


Figure 6. Drain−to−Source Leakage Current vs. Voltage

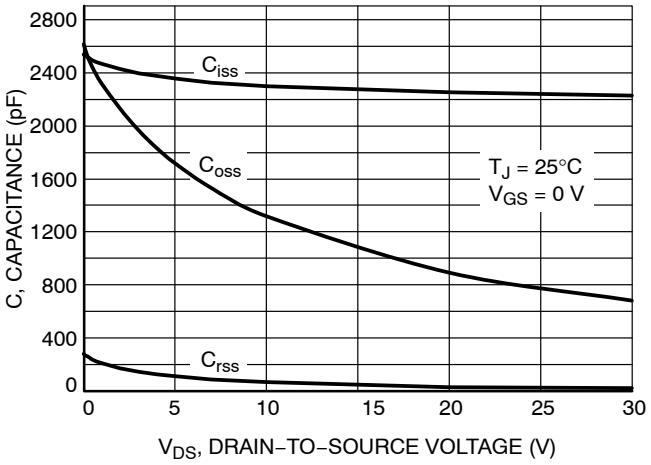


Figure 7. Capacitance Variation

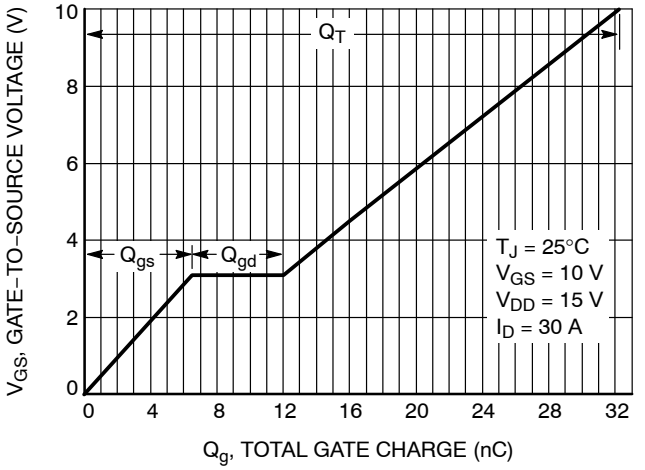


Figure 8. Gate−to−Source and Drain−to−Source Voltage vs. Total Charge

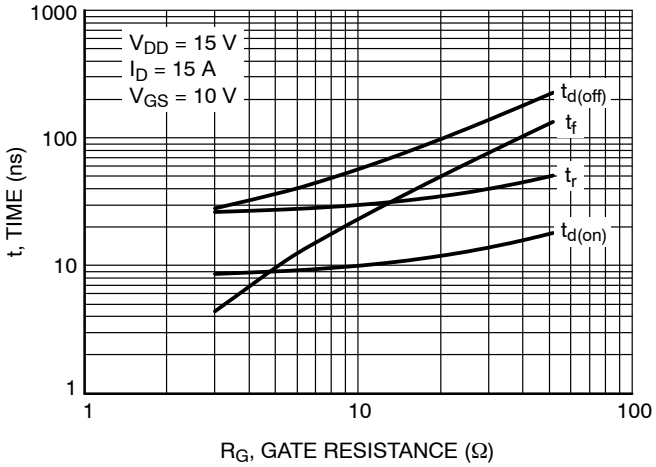


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

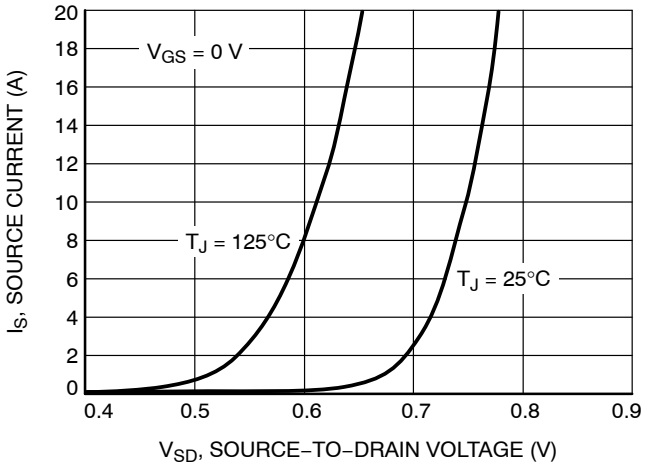


Figure 10. Diode Forward Voltage vs. Current

TYPICAL CHARACTERISTICS

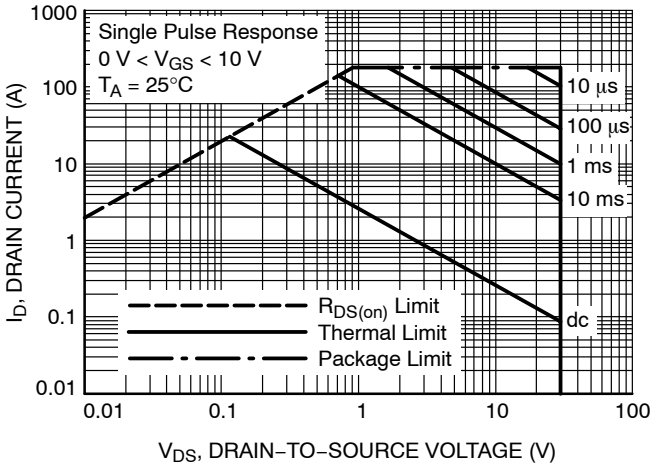


Figure 11. Maximum Rated Forward Biased Safe Operating Area

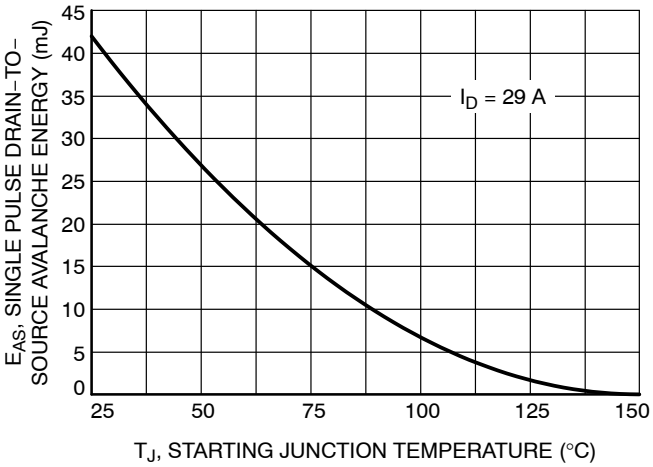


Figure 12. Maximum Avalanche Energy vs. Stating Junction Temperature

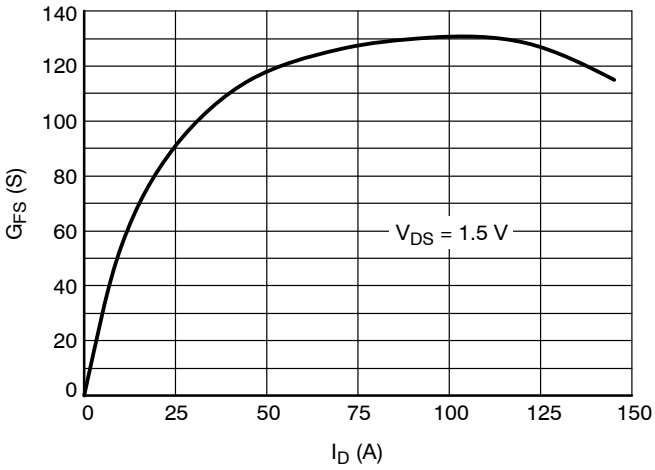


Figure 13. G_{FS} vs. I_D

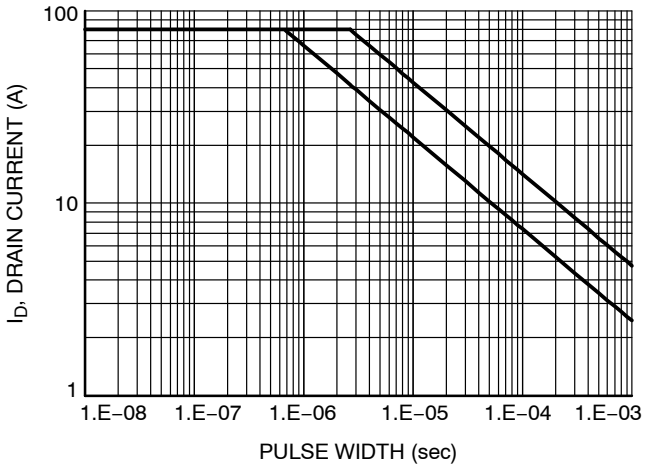


Figure 14. Avalanche Characteristics

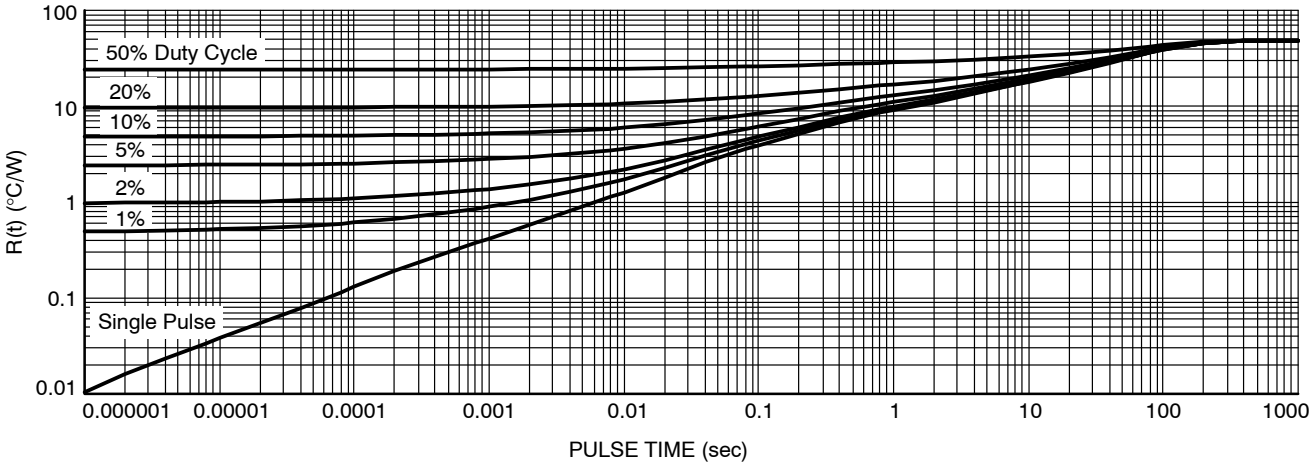
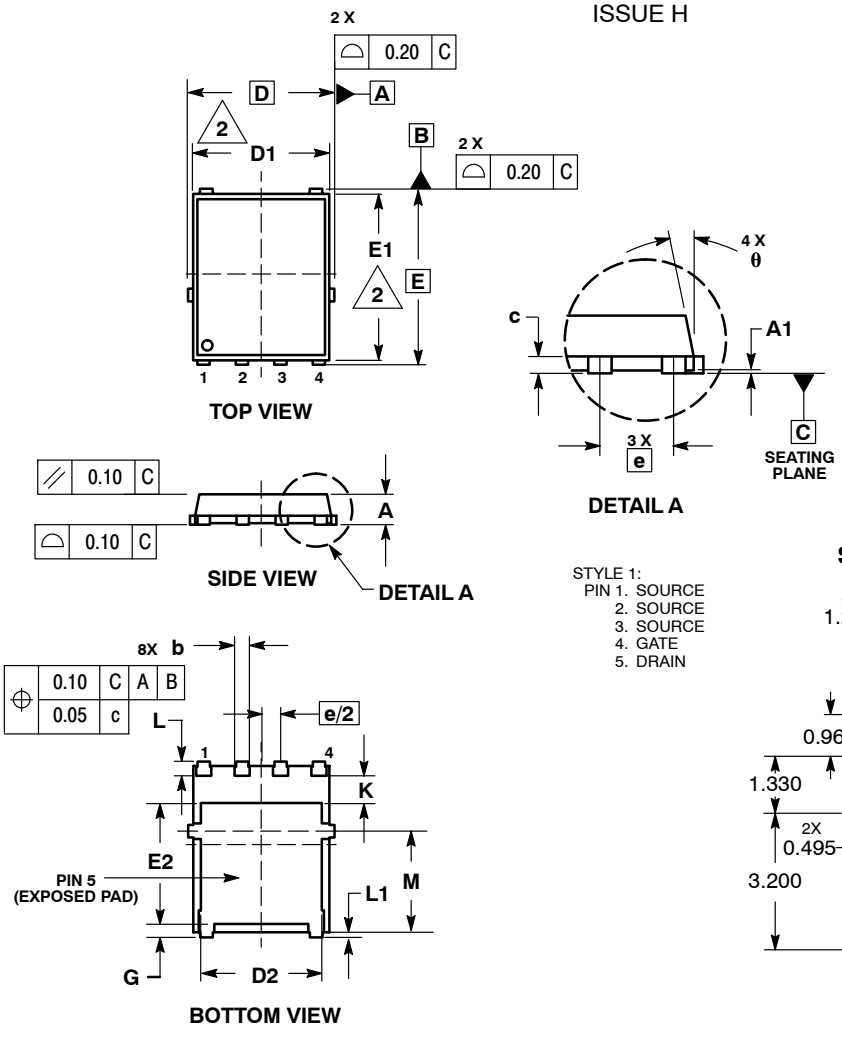


Figure 15. Thermal Response

PACKAGE DIMENSIONS

DFN5 5x6, 1.27P
(SO−8FL)
CASE 488AA
ISSUE H

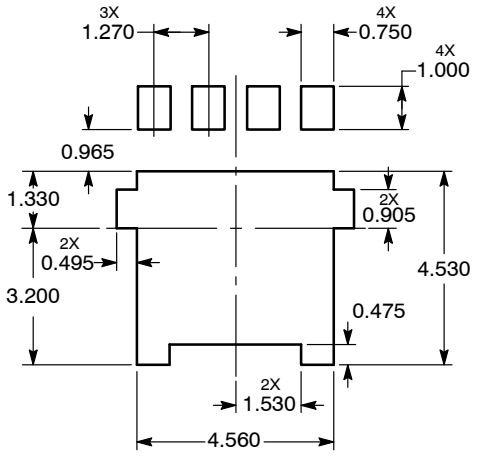


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D		5.15 BSC	
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E		6.15 BSC	
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e		1.27 BSC	
G	0.51	0.61	0.71
K	1.20	1.35	1.50
L	0.51	0.61	0.71
L1	0.05	0.17	0.20
M	3.00	3.40	3.80
θ	0 °	---	12 °

STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

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